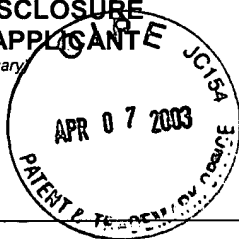


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Application Number	09/944981
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Lindsay, Walter

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Attorney Docket No: 1303.021US1

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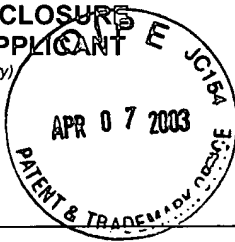
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Examiner Name	Lindsay, Walter

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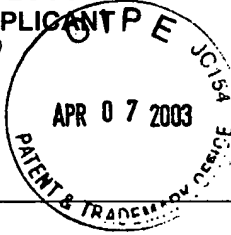
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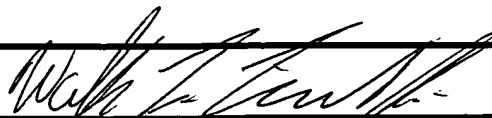
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